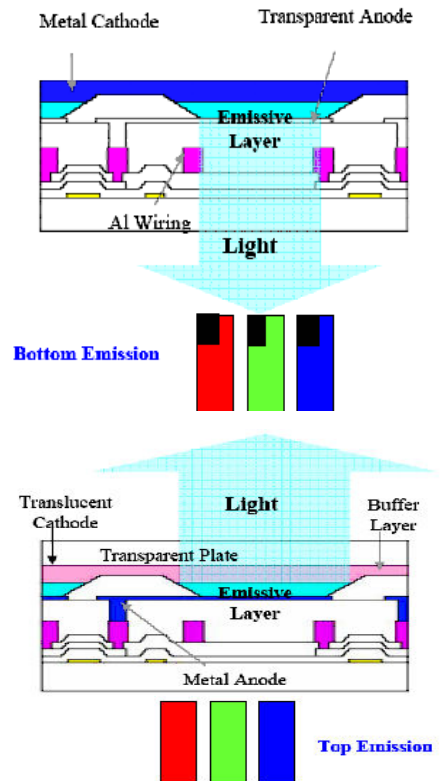


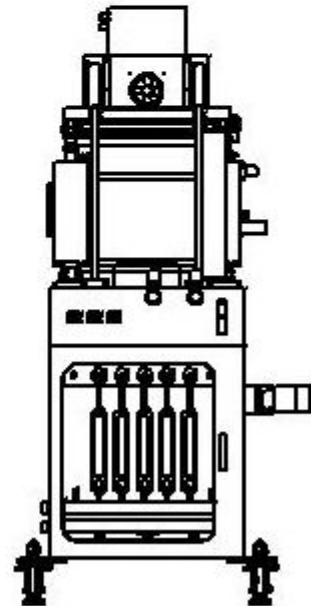
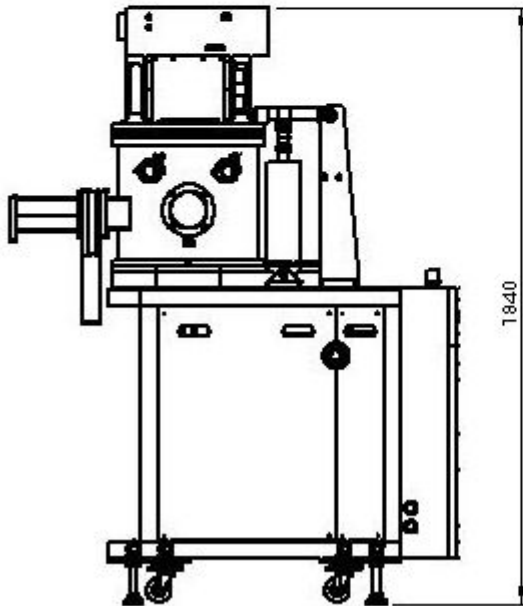
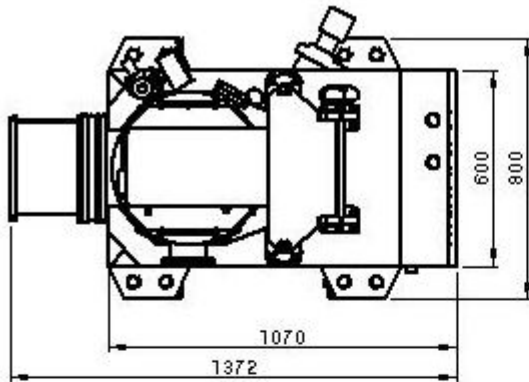
ATS-CVD Series PECVD System for OLED Barrier Layers



Special Features

- ◆ SiO_x and SiN_x rf-PECVD system for R&D and small scale production
- ◆ Designed to be compatible with OLED cluster system
- ◆ Transformer-coupled high density plasma source
- ◆ System and process controlled automatically by PC
- ◆ Applications
OLED barrier layers
(ex. SiO_x, SiN_x, SiON_x, etc)
- ◆ Substrate
100x100mm², 150x150mm² glass
- ◆ Average throughput
Up to 5,000 substrates per year
- ◆ Dimension
1,400L × 1,900H × 2,000W (mm³)
- ◆ Others
 - Power : AC 3kW for TCP source
(13.56MHz)
 - AC 600W for bias
(13.56MHz)
 - Deposition gas
:SiH₄/NH₃/N₂/N₂O/O₂/He/H₂
 - Chamber cleaning gas: NF₃/N₂O/O₂
 - Heater : silicon carbide
(heating rate: 40°C/min,
max. temp.: 800°C, temp.
deviation : negligible)
 - Pump : dry(2,000l/min) & turbo(1,200l/s)

◇ Layout



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